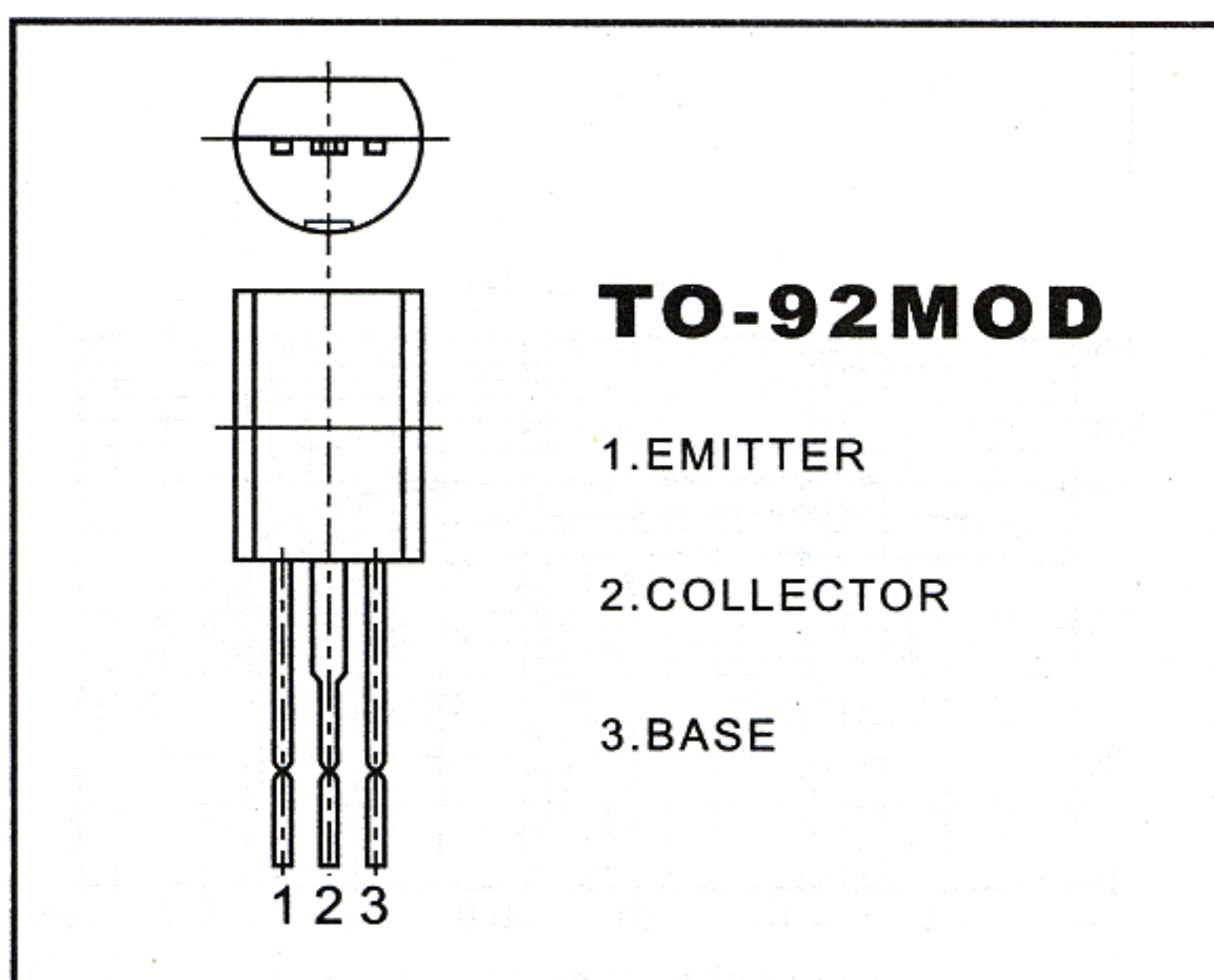


2SA966 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.9W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1 \text{ mA}, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1 \text{ mA}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30 \text{ V}, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2 \text{ V}, I_C = -500 \text{ mA}$	100	320	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -1.5 \text{ A}, I_B = -0.03 \text{ A}$		-2	V
Base-emitter voltage	V_{BE}	$I_C = -500 \text{ mA}, V_{CE} = -2 \text{ V}$		-1	V
Transition frequency	f_T	$V_{CE} = -2 \text{ V}, I_C = -500 \text{ mA}$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

